MA MOSPEC

Switchmode Dual High Efficiency Power Rectifiers

... Designed for use in switching power supplies. inverters and as free wheeling diodes. These state-of-the-art devices have the following features:

- * High Surge Capacity
- * Low Power Loss, High efficiency
- * Glass Passivated chip junctions
- * 150 °C Operating Junction Temperature
- * Low Stored Charge Majority Carrier Conduction
- * Low Forward Voltage , High Current Capability
 * High-Switching Speed 75 & 100 Nanosecond Recovery Time
- * Plastic Material used Carries Underwriters Laboratory

MAXIMUM RATINGS

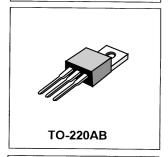
Characteristic	Symbol H16C					Unit
		30	40	50	60	1
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	300	400	500	600	V
RMS Reverse Voltage	V _{R(RMS)}	210	280	350	420	V
Average Rectifier Forward Current Per Leg T _c =125°C Per Total Device	I _{F(AV)}	8.0 16			А	
Peak Repetitive Forward Current (Rate V _R , Square Wave, 20kHz, T _c =125°C)	 FM	16			Α	
Non-Repetitive Peak Surge Current (Surge applied at rate load conditions halfware,single phase,60Hz)	 FSM	125				Α
Operating and Storage Junction Temperature Range	T _j , T _{stg}	- 65 to + 150			°C	

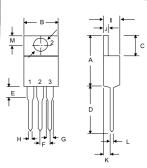
ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	H16C				Unit
		30	40	50	60	
Maximum Instantaneous Forward Voltage (I_F =8.0 Amp, T_C = 25 $^{\circ}$ C) (I_F =8.0 Amp, T_C = 100 $^{\circ}$ C)	V _F	1.30 1.12		1.50 1.34		V
Maximum Instantaneous Reverse Current (Rated DC Voltage, T _c = 25 °C) (Rated DC Voltage, T _c = 125 °C)	I _R	10 500				uA
Reverse Recovery Time ($I_F = 0.5 \text{ A}$, $I_R = 1.0$, $I_{rr} = 0.25 \text{ A}$)	T _{rr}	75 100		100	ns	
Typical Junction Capacitance (Reverse Voltage of 4 volts & f=1 MHz)	C _P	70			pF	

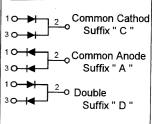
HIGH EFFICIENCY **RECTIFIERS**

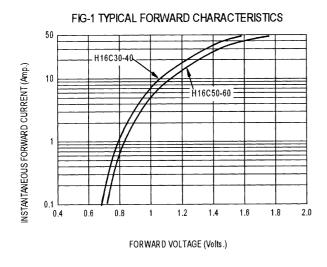
16 AMPERES 300 -- 600 VOLTS

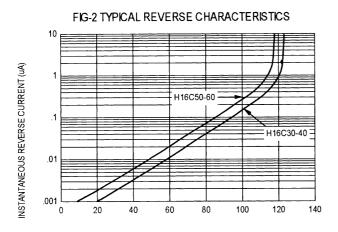


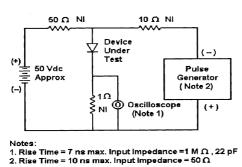


·	MILLMETERS			
DIM	MIN	MAX		
Α	14.68	15.32		
В	9.78	10.42		
С	6.01	6.52		
D	13.06	14.62		
Ε	3.57	4.07		
F	2.42	2.66		
G	1.12	1.36		
Н	0.72	0.96		
ı	4.22	4.98		
J	1.14	1.36		
K	2.20	2.97		
L	0.33	0.55		
М	2.48	2.98		
0	3.70	3.90		

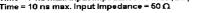


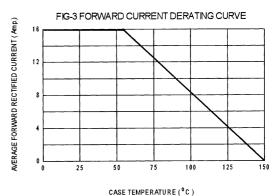


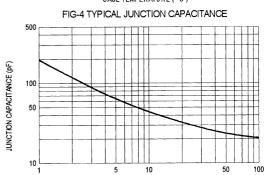


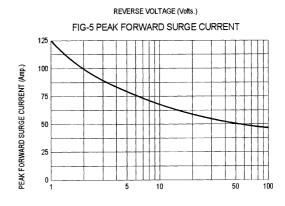


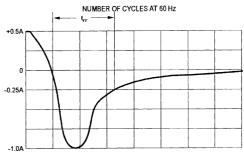
PERCENT OF PEAK REVERSE VOLTAGE(%)











Set time base for 20/50 ns/div

Fig-6 Reverse Recovery Time Characteristic and Test Circuit Diagram



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